



COPY OF PAGES
ORIGINALLY FILED

#51/Amend E
8/1/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Thomas A. Figura, Kevin Donohoe, & Thomas Dunbar

Serial No.: 09/471,460

Filed: December 22, 1999

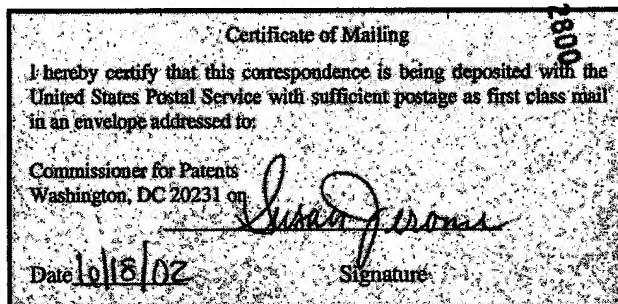
Title: USE OF A PLASMA SOURCE TO FORM A LAYER
DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

§
§ Group Art Unit: 2825
§
§ Application Examiner: Calvin Lee
§
§ Atty. Docket: 94-0280.03
§
§
§
§
§
§

RECEIVED
JUL -3 2002
TECHNOLOGY CENTER 2800

AMENDMENT AND RESPONSE TO THE
OFFICE ACTION DATED MARCH 20, 2002

Commissioner for Patents
Washington, D.C. 20231



Dear Sir:

Applicants submit this Amendment and Response to the Office Action dated March 20, 2002. Please amend the above-captioned application as follows.

IN THE CLAIMS

Please amend the claims to the form described below.

45. (Thrice amended) A method of providing a material in a site between metal features on a wafer, comprising:

performing a deposition of said material over said wafer in said site;

and

etching said material in the same general site used to perform said deposition,

wherein said step of etching further comprises etching generally

simultaneously with performing said deposition.

El